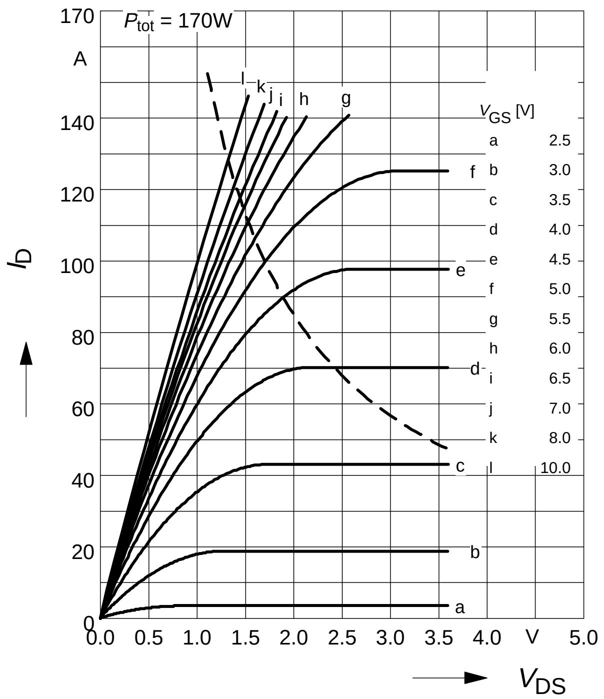
Typ. output characteristics

$I_D = f(V_{DS})$

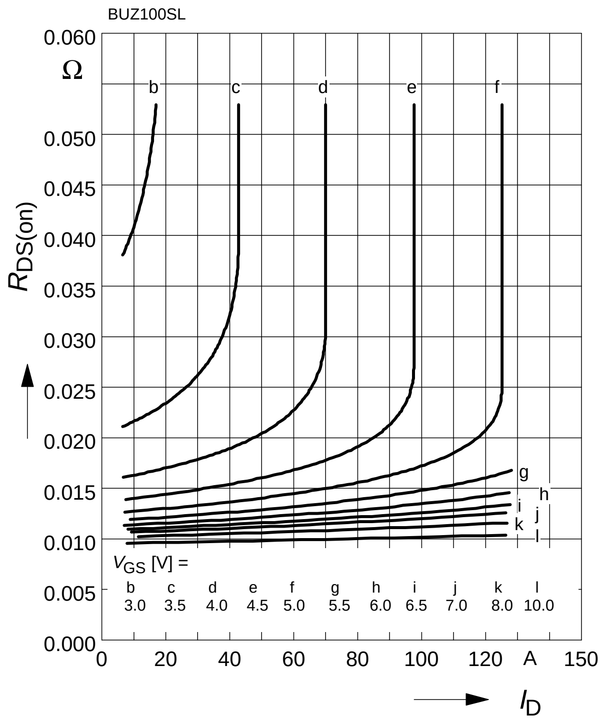
parameter: t_p = 80 µs



Typ. drain-source-on-resistance

$R_{DS(on)} = f(I_D)$

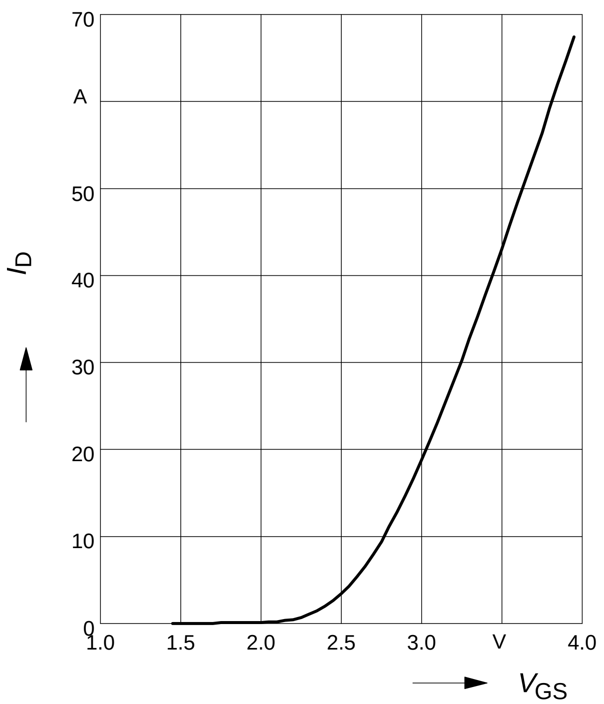
parameter: V_{GS}



Typ. transfer characteristics $I_D = f(V_{GS})$

parameter: t_p = 80 µs

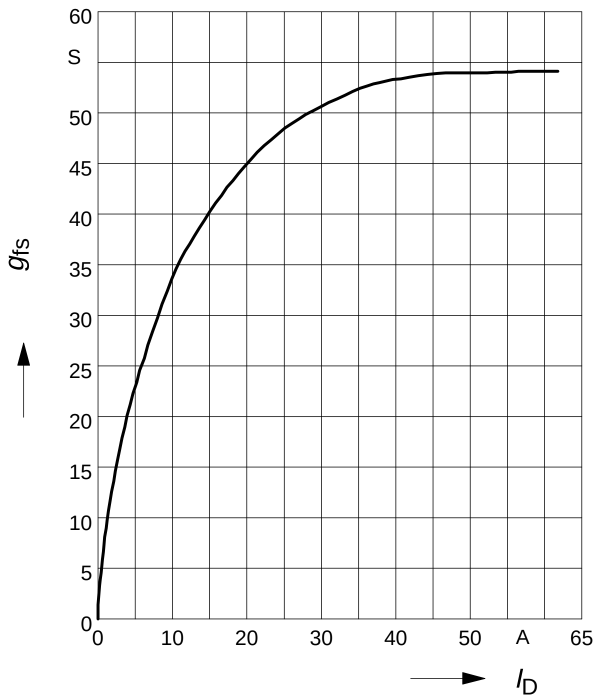
$V_{DS} \geq 2 \times I_D \times R_{DS(on)max}$



Typ. forward transconductance

$g_{fs} = f(I_D)$; T_j = 25°C

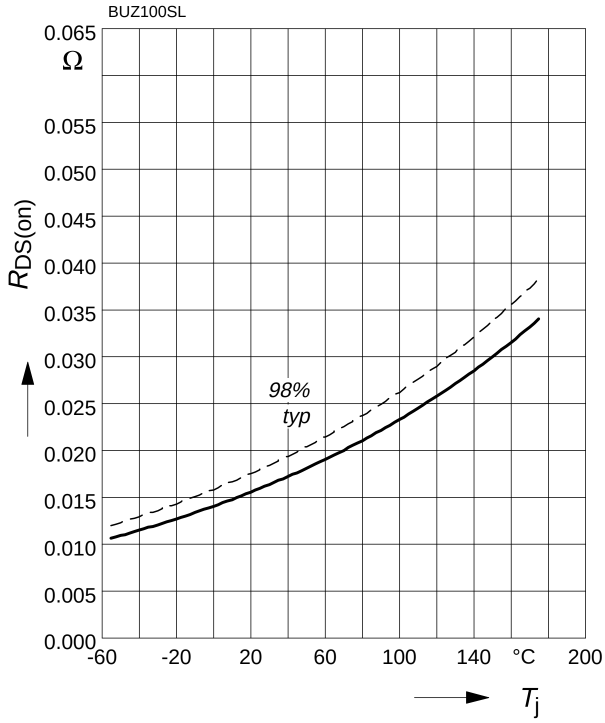
parameter: g_{fs}



Drain-source on-resistance

$R_{DS(on)} = f(T_j)$

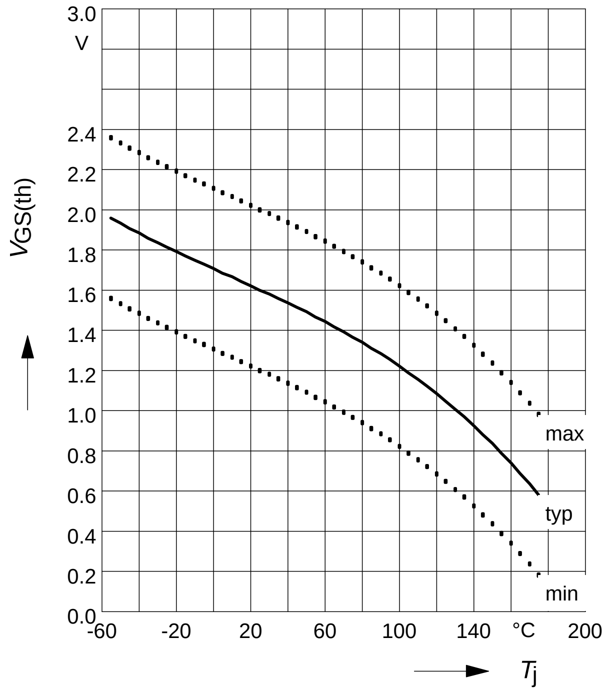
parameter : I_D = 50 A, V_{GS} = 4.5 V



Gate threshold voltage

$V_{GS(th)} = f(T_j)$

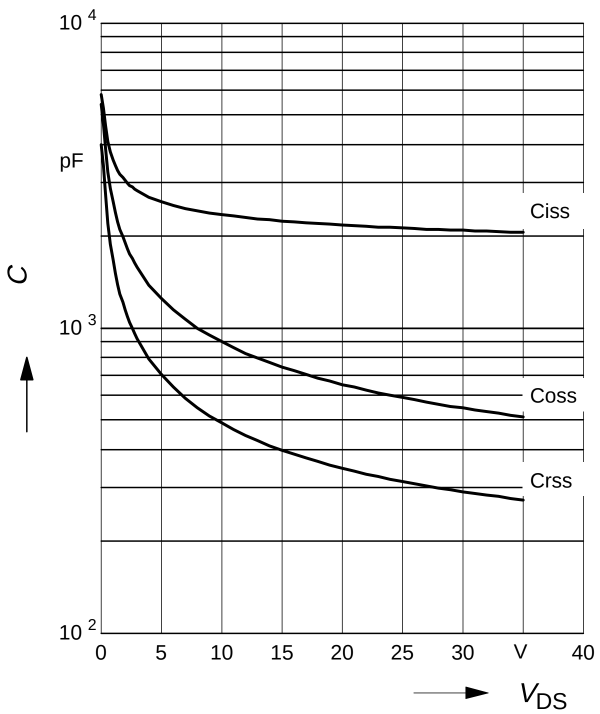
parameter : $V_{GS} = V_{DS}$, I_D = 130 µA



Typ. capacitances

$C = f(V_{DS})$

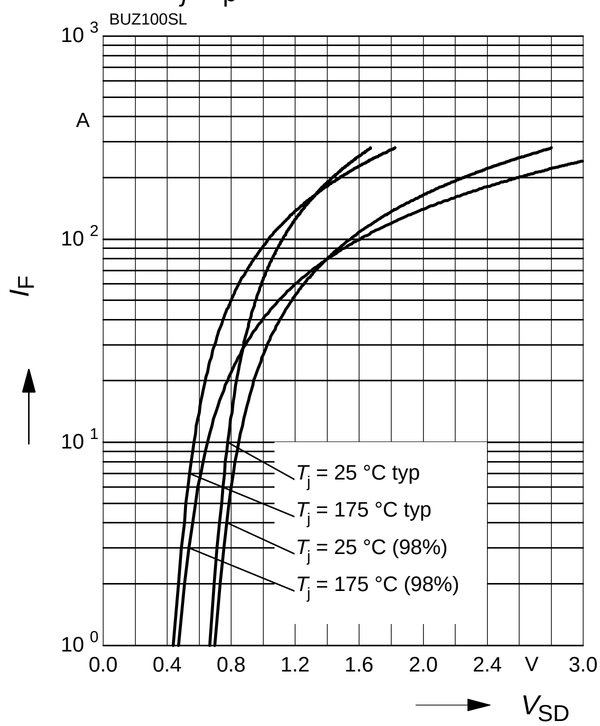
Parameter: V_{GS} = 0 V, f = 1 MHz



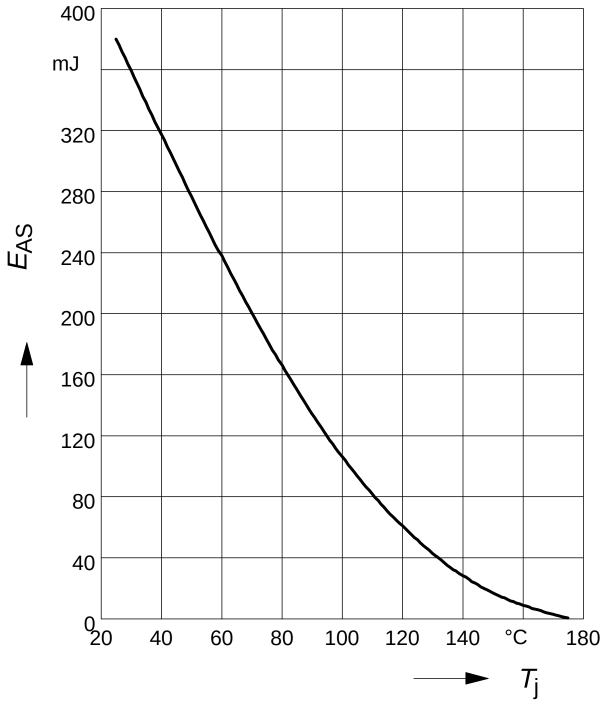
Forward characteristics of reverse diode

$I_F = f(V_{SD})$

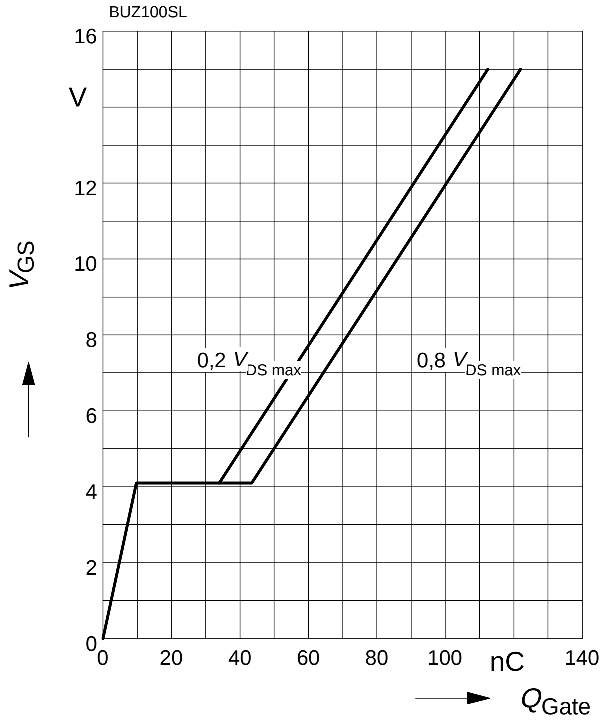
parameter: T_j , t_p = 80 µs



Avalanche Energy $E_{AS} = f(T_j)$
parameter: I_D = 70 A, V_{DD} = 25 V
R_{GS} = 25 Ω



Typ. gate charge
$V_{GS} = f(Q_{Gate})$
parameter: $I_{D\ puls}$ = 70 A



Drain-source breakdown voltage
$V_{(BR)DSS} = f(T_j)$